Microwave Rectification of the Current at the Metal-Metal Junction for Dilute 2D Metals

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Within a quasiclassical transport theory for 2D electron system we analyze a recently observed effect of microwave rectification at the boundary between two 2D metals of different carrier densities. Nonlinear response is employed to explain the effect. It is shown that the effect of rectification arises due to inhomogeneity of the electron density which breaks space symmetry of the system. The results agree with the above experiments.

PACS numbers: 71.30, 73.40, 73:50

At present there is an increasing interest in studies of nonlinear effects in transport phenomena. These studies may lead to many novel results and have important applications such as the unidirectional transport of molecular motors in the biological realm [1] and other kinds of noise induced chaotic transport [2], and electronic transport through superlattices [3], to mention a few. It is shown that when some space-time symmetries characterizing a system under study are broken, this can give rise to a nonlinear response of such system to an external disturbance [1,4-8].

The present work is motivated with the results of recently reported experiments [9]. A nonlinear response of a dilute 2D electron system of a significantly nonuniform electron density $n(r)$ to an alternating electric field $E(t)$ including the rectification of the current was observed in these experiments. The inhomogeneity in the electron density was produced in the experiments by the applied gates voltage. As a result the density was monotonically varying along a direction perpendicular to the lines of the applied electric potential taking on values between $2 \quad 10^{11}$ and $8 \quad 10^{11} cm^{-2}$: Here we show that the effect of rectification can be provided by the electron density gradient $r n(r)$.

It is well known that when two conductors of different carrier densities, and, therefore, of different work functions are put in contact, the contact has a nonlinear current voltage characteristic which provides the rectification of high-frequency currents flowing through the interface. The theory of the rectification properties of metal-metal junctions is well developed (See e.g. [10]). Usually the rectification is attributed to electron tunneling through the potential barrier at the metal-metal interface. However, semiclassical analysis of the rectification through a metal-metal interface, based on the Boltzmann transport equation also was carried out [11-13]. These theories are applicable when a width of the junction is small compared to characteristics of the electron transport.

However, in the experiments of [9] both mean free path of electrons l and the width d of the slit separating the regions of smaller electron density n_1 and larger density n_2 are of the same order ($10^{-5} cm$). More thorough estimation showes that in these experiments $d \quad l$; and the ratio $d=l$ could take on values close to 5. Therefore we consider the case when the electron density varies slowly enough, so that the length of the interval d where $r n$ significantly differs from zero is large compared to the mean free path of electrons. As a first approximation we assume that $d >> l$ in further analysis.

To simplify following calculations we introduce a simple model where a pair of 2D metals contiguous through the conducting boundary is replaced by a single metal of strongly inhomogeneous electron density. Then both electron density and the chemical potential (r) depend on "r" ($(r) = n(r)=D_0$; where D_0 is the electron density of states at the Fermi surface).

We treat electrons included into the considered 2D system as noninteracting quasiparticles obeying classical dynamics and subject to external forces and friction. Their motion is described with the equation

$$\frac{dp}{dt} + er V(r) \quad eE(t) + \quad p = 0: \qquad (1)$$

Here, p is the electron quasimomentum, and $V(r)$ is the applied voltage producing the inhomogeneity in the electron density. The friction term in the equation of motion (1) is written in a simplest form $\quad p$ where $\quad$ is the characteristic relaxation frequency of the electron system. In fact, this term describes changes in the quasimomentum of a single electron due to its scattering. When there is no alternating electric field $E(t)$ the electron system is in the local equilibrium maintained with an internal electrochemical field $\frac{1}{e} r \quad (r) = r n(r)=eD_0$ which balances the external field $\quad r V(r)$: The presence of the field $E(t)$ violates this balance. However, when the alternating contribution to the external electric field $E(t)$ is weak compared to the static contribution $\quad r V(r)$; the latter is still nearly equal to the electrochemical field arising in the 2D electron system, and we can replace the second term in the equation (1) by $r n(r)=D_0$:

Assuming for simplicity that $E(t)$ is directed in parallel with the electron density gradient (along the "x" axis in a chosen coordinate system) we rewrite the equation (1)

in the form

$$\frac{d^2x}{dt^2} + \quad \frac{dx}{dt} \quad \frac{1}{m D_0}\frac{dn}{dx} \quad \frac{e}{m}E(t) = 0 \qquad (2)$$

where m is the electron effective mass. Symmetries of such equations were analyzed in detail in earlier works [5–8]. It was shown there that for asymmetric space dependent force — in our case this force equals $\frac{1}{D_0}\frac{dn}{dx}$ — system of quasiparticles obeying equation of motion of the form (2) could give a nonlinear and asymmetric adiabatic response to the ac field $E(t)$ including a dc contribution to the current regardless of symmetries of $E(t)$ if dissipation is included ($\neq 0$): Within the dissipationless limit ($= 0$) the effect of rectification disappears when the ac field possesses E_s symmetry defined as $E(t+\ ) = E(\ t+\ )$ even in the case when the spatial symmetry is broken. However, in further analysis we rule this case out assuming that the dissipation constant takes on nonzero values.

In the experiments of [9] the applied gates voltage produced an aperiodic profile of the electron density as it depends on space coordinates. Therefore the density gradient $r\,n(r)$ also is aperiodic. Assuming that $r\,n(r)$ is asymmetric (and there are no grounds for otherwise anticipations) we can expect the rectification of the current to be revealed in the response to the microwave field $E(t)$ for $\neq 0$:

To get the desired response of the electron system we use the Boltzmann transport equation for the electron distribution function $f(r;p;t)$ taken within the relaxation time approximation:

$$\frac{@f}{@t} + \frac{v@f}{@r} + \frac{dp}{dt}\frac{@f}{@p} = \quad \frac{f \quad f_{eq}}{} \qquad (3)$$

where the function f_{eq} describes the local equilibrium state of the electron system in the absence of the microwave radiation $E(t)$ and equals the Fermi distribution function:

$$f_{eq} = f_0(\text{"}; (r); T): \qquad (4)$$

Here, $= p^2=2m$ is the quasiparticle energy. In further calculations it is supposed that the relaxation time is finite and nonzero to provide dissipation to be included [14].

Following [4] we expand $f(r;p;t)$ in harmonic polynomials, keeping three first terms of the expansion:

$$f(r;p;t) = f_{eq} + f_1\ p\ + f_2 \quad p\ p \quad \frac{p^2}{2} \quad : \qquad (5)$$

The coefficients $f_1; f_2$ depend on the difference $\text{"} \quad (r)$, and the time; $\ ; \ = x;y$:

Such approximation is justified for a weak microwave field because next terms of the expansion give smaller corrections in terms of the microwave field magnitude. Substituting this expansion into Boltzmann equation we get a set of equations:

$$\frac{@f_1}{@t} + \frac{e}{m}E \quad (t)\frac{@f_{eq}}{@\text{"}} + 2e \ E \quad (t) + \frac{1}{e}\frac{@}{@r} \quad f_2$$

$$e\frac{p^2}{2m}E \quad (t)\frac{@f_2}{@\text{"}} \quad = \quad \frac{f_1}{}; \qquad (6)$$

$$\frac{@f_2}{@t} + \frac{e}{m}E \quad (t)\frac{@f_1}{@t} = \quad \frac{f_2}{}: \qquad (7)$$

Here the term $\frac{1}{e}\frac{@}{@r} = \frac{1}{eD_0}\frac{@n}{@r}$ describes the internal "electrochemical" field arising due to inhomogeneity of the electron density. To proceed we take the microwave field $E(t)$ of frequency $!$ as:

$$E(t) = \frac{1}{2}(E_! e^{i!t} + E_! e^{\ i!t}) \qquad (8)$$

Here, $E_! = E^0_! + iE^{00}_!$. Further we assume that $! \ < 1$ to provide the adiabatic response. This does not contradict the relevant experiments of [9]. Symmetry propeties of the Boltzmann transport equation were analyzed before [7], and it was shown that they completely agree with the symmetries of the initial equations of motion of relevant particles. In the present analysis we stipulate that the density gradient $r\,n(r)$ is asymmetric and aperiodic and the relaxation time is finite, so we can expect the current rectification to be exhibited.

We expand the coefficients $f_1; f_2$ in time Fourier series. Then, solving the system (6), (7) by perturbation theory we present the current density j:

$$j = \frac{2e}{m^2(2\ h)^2} \int f_1\ p\ p\ d^2p \qquad (9)$$

as an expansion in powers of the microwave magnitude $E_!$: Besides the term which describes a linear response of the electron system to the alternating field, this expansion includes a dc term $j_{(1)}$ corresponding to the rectified current density:

$$j_{(1)} = \quad \frac{e^3\ ^3}{m^2}\frac{R + ! \ Q}{1 + (! \ )^2} \qquad (10)$$

and the term $j_{(2)}$ which describes the current density at the doubled frequency $2!$:

$$j_{(2)} = \quad \frac{e^3\ ^3}{m^2}\frac{1}{(1 + (! \ )^2)(1 + 4(! \ )^2)^2}$$

$$1 \quad 8(! \ )^2 \quad R\cos 2!t \quad Q\sin 2!t$$

$$+ ! \quad 5 \quad 4(! \ )^2 \quad R\sin 2!t + Q\cos 2!t \qquad (11)$$

where

$$R(E_\omega) = E'_\omega(E'_\omega \quad rn) + E''_\omega(E''_\omega \quad rn)$$

$$Q(E_\omega) = E''_\omega(E'_\omega \quad rn) \quad E'_\omega(E''_\omega \quad rn): \qquad (12)$$

Both nonlinear contributions are quadratic in E_ω; and they originate from the inhomogeneity in the electron density. When rn goes to zero, the rectification disappears. Within a low frequency limit $\omega \ll 1$ the nonlinear contributions to the currents (10), (11) do not vanish. This brings an asymmetry into the current-voltage characteristics of the unhomogeneous electron system, even for $\omega \to 0$: Similar results were obtained in earlier works for different mechanisms of the rectification. We also can estimate an average of the rectified contribution to the current density over the space interval d: The averaged quantities $< R(E_\omega) >$ and $< Q(E_\omega) >$ are proportional to $(n_2 \quad n_1)/d$: This confirms that an asymmetric profile of the electron density can give rise to the effect of the current rectification. However, the obtained results are valid only for small magnitudes of the microwave field, when the quadratic in E_ω terms in the expansion for the current density are smaller than the linear term. Therefore the asymmetry of the current-voltage characteristic at the low-frequency limit may be unavailable for observations.

The nonlinear contributions to the current densities $j_{(1)}; j_{(2)}$ occur when the microwave field has a component directed perpendicularly to the boundary between 2D metals. Otherwise they both turn zero. It also follows from (10)–(12) that the direction of the currents reverses when we reverse the polarity of the gates, and, consequently rn: This agrees with the experimental results [9].

To make a comparison of the present results with the experiments [9] we roughly estimate a voltage V_{dc}; which corresponds to the rectified current. Assuming that the microwave field is applied along the "x" direction as well as rn we arrive at the estimation:

$$jV_{dc}j = \int_{\quad 1}^{1} \frac{j_{dc}(x)}{\sigma_0(x)} dx : \qquad (13)$$

Here $\sigma_0(x)$ is the Drude conductivity for the electron density $n(x)$ and relaxation time $\tau(x)$:

It was reported [9] that when the minimum $n(x)$ is larger than a certain value n_0 ($n_0 \quad 2{:}5 \quad 10^{11} \frac{1}{cm^2}$) the relaxation time τ is nearly independent on the electron concentration and can be treated as a constant in carrying out integration over "x"in (11). Using this approximation we get:

$$jV_{dc}j \quad \frac{4}{m}\frac{e}{}^2 \ln\frac{n_1}{n_2} E_\omega^2 : \qquad (14)$$

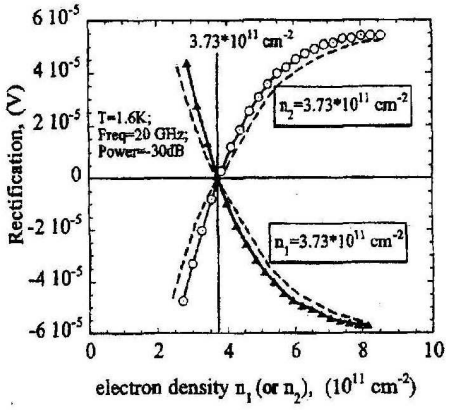

FIG. 1: The rectified signal voltage V_{dc} is plotted versus electron density. Solid lines { experiment of Ref.[9]; dashed line { theory for the parameters $m \quad 0{:}2m_0$; $\quad 3 \quad 10^{12} s^{1}$:

The above estimate provides a reasonable agreement with the results of [9] concerning the dependence of the rectification signal on the electron densities of contiguous 2D – metals, as shown in Fig.1. Plotting curves in this figure we assumed in accordance with [9] that $m \quad 0{:}2m_0$ (m_0 is the mass of a free electron); $\quad 3 \quad 10^{12} s^{1}$ and $E_\omega \quad 10^3 \frac{V}{m}$:

In summary, obtained results based on the Boltzmann equation exhibit the effect of the microwave rectification of the current in a 2D electron gas. It is shown that the effect of rectification can originate from the inhomogeneity of the electron density. The effect appears when an asymmetric density gradient is created in the electron system by an external static voltage applied to it. The dc current arises when the ac electric field $E(t)$ has a nonzero component along the density gradient. The results of theoretical analysis agree with the recently reported experimental results [9].

Acknowledgments. I thank M.R. Sarachik for enabling me to study the relevant experimental results and helpful discussions and G.M. Zimbovsky for help with the manuscript.

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